

UNISONIC TECHNOLOGIES CO., LTD

BCV47

Preliminary

NPN SILICON TRANSISTOR

NPN DARLINGTON TRANSISTOR

DESCRIPTION

The UTC BCV47 is a NPN Darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

FEATURES

- * Medium current: max. 500mA
- * Low voltage: max. 60V

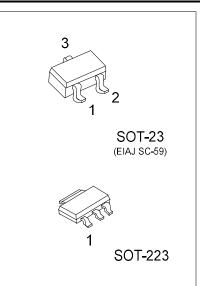
ORDERING INFORMATION

Ordering Number		Deekere	Pin Assignment			Deeking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BCV47L-AA3-R	BCV47G-AA3-R	SOT-223	В	С	E	Tape Reel	
BCV47L-AE3-R	BCV47G-AE3-R	SOT-23	В	Е	С	Tape Reel	
Note: Pin Assignment: B: Base C: Case E: Emitter							

	Packing Type Package Type	(1) R: Tape Reel (2) AA3: SOT-223, AE3: SOT-23
(3)0	Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING

SOT-23	SOT-223		
BC47	BCV47 L: Lead Free G: Halogen Free Date Code		



■ ABSOLUATE MAXIUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	80	V
Collector-Emitter Voltage		V _{CES}	60	V
Emitter-Base Voltage		V _{EBO}	10	V
Base Current		IB	100	mA
Collector Current (DC)		lc	500	mA
Peak Collector Current		I _{CM}	800	mA
Collector Power Dissipation	SOT-223	D D	600	mW
(Note 2)	SOT-23	- Pc	250	mW
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-65 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Transistor mounted on an FR4 printed-circuit board.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	SOT-223	θ _{JA}	208.3	°C/W	
	SOT-23		500	°C/W	
Junction to Case	SOT-223	θ _{Jc}	20	°C/W	
	SOT-23		100	°C/W	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA	80			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =10mA	60			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =10μA	10			V
Collector Cut-off Current	I _{CBO}	V_{CBO} =60V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =10V, I _E =0			100	nA
DC Current Gain (Note)		V _{CE} =5V, I _C =1mA	2000			
	h _{FE}	V _{CE} =5V, I _C =10mA	4000			
		V _{CE} =5V, I _C =100mA	10000			
Collector-Emitter Saturation Voltage	V _{CE(SAT})	I _C =100mA, I _B =0.1mA			1	V
Base-Emitter Saturation Voltage (Note)	V _{BE(SAT)}	I _C =100mA, I _B =0.1mA			1.5	V
Base Emitter On Voltage (Note)	V _{BE(ON)}	I _C =10mA, V _{CE} =5V			1.4	V

Note: Pulse test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.



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